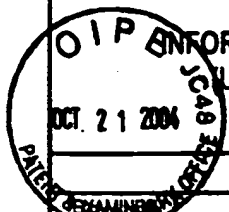


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		APPLICANT(S): WARD D. PARKINSON AND ALLEN BENN						
		FILING DATE: August 4, 2003		GROUP ART UNIT: 2827				
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APPLICANT(S)
Ward D. Parkinson et al.

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EXAMINER

V. Nguyen

DATE CONSIDERED

4/3/2005

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